CPH6444

N-Channel Power MOSFET 60V, 4.5A, 78mΩ, Single CPH6



http://onsemi.com

Features

- · Low ON-resistance
- 4V drive

- · Protection diode in
- · Halogen free compliance

Specifications

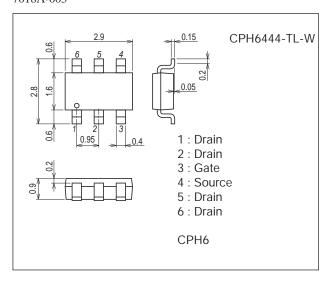
Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|------------------|---|-------------|------|
| Drain to Source Voltage | V _{DSS} | | 60 | V |
| Gate to Source Voltage | VGSS | | ±20 | V |
| Drain Current (DC) | ID | | 4.5 | Α |
| Drain Current (Pulse) | IDP | PW≤10μs, duty cycle≤1% | 18 | А |
| Allowable Power Dissipation | PD | When mounted on ceramic substrate (900mm ² x0.8mm) | 1.6 | W |
| Channel Temperature | Tch | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

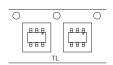
unit : mm (typ) 7018A-003



Ordering & Package Information

| Device | Package | Shipping | memo |
|--------------|--------------------------------|--------------------|--------------------------------|
| CPH6444-TL-W | CPH6 SC-74, SOT-26, SOT-457 | 3,000 pcs./reel | Pb-Free and Halogen Free |

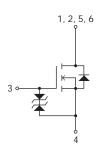
Packing Type: TL



Marking



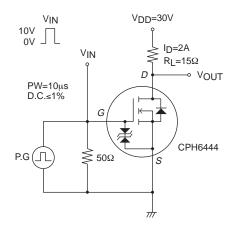
Electrical Connection

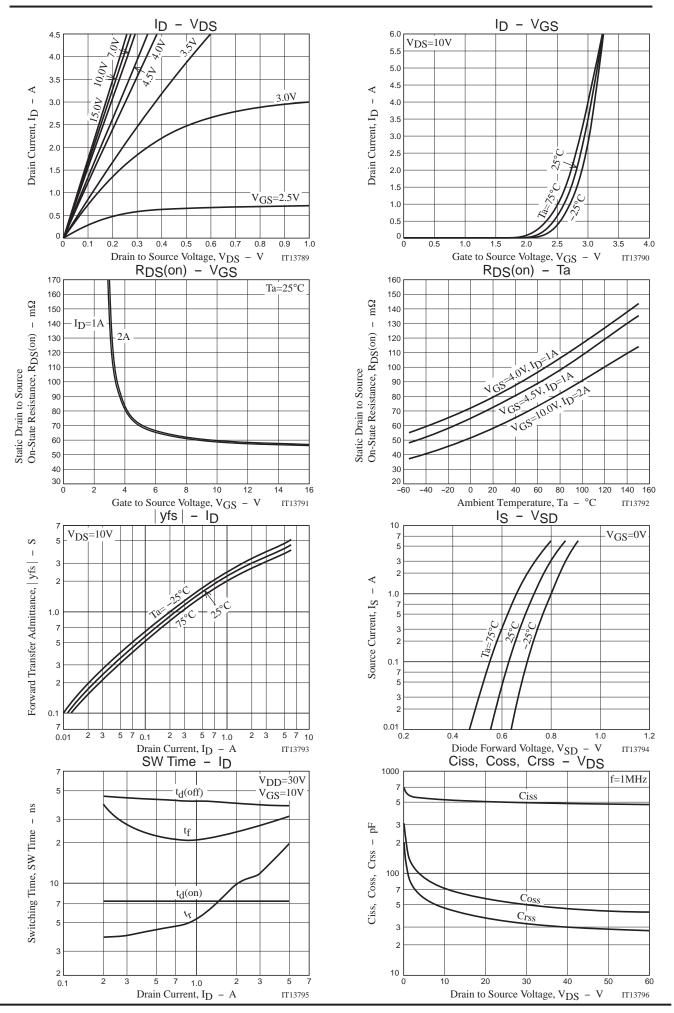


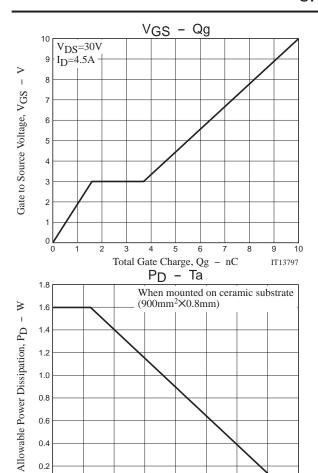
Electrical Characteristics at Ta=25°C

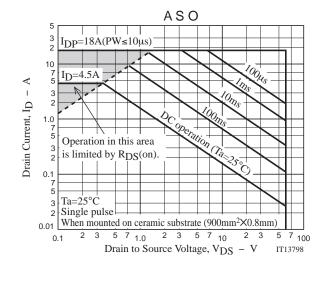
| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--|-----------------------|--|---------|------|-----|------|
| | | | min | typ | max | Unit |
| Drain to Source Breakdown Voltage | V(BR)DSS | ID=1mA, VGS=0V | 60 | | | V |
| Zero-Gate Voltage Drain Current | IDSS | V _{DS} =60V, V _{GS} =0V | | | 1 | μΑ |
| Gate to Source Leakage Current | IGSS | V _{GS} =±16V, V _{DS} =0V | | | ±10 | μΑ |
| Cutoff Voltage | VGS(off) | V _{DS} =10V, I _D =1mA | 1.2 | | 2.6 | V |
| Forward Transfer Admittance | yfs | V _{DS} =10V, I _D =2A | 1.8 | 3 | | S |
| Static Drain to Source On-State Resistance | R _{DS} (on)1 | I _D =2A, V _{GS} =10V | | 60 | 78 | mΩ |
| | R _{DS} (on)2 | I _D =1A, V _G S=4.5V | | 74 | 104 | mΩ |
| | R _{DS} (on)3 | ID=1A, VGS=4V | | 81 | 114 | mΩ |
| Input Capacitance | Ciss | V _{DS} =20V, f=1MHz | | 505 | | pF |
| Output Capacitance | Coss | | | 57 | | pF |
| Reverse Transfer Capacitance | Crss | | | 37 | | pF |
| Turn-ON Delay Time | t _d (on) | See specified Test Circuit. | | 7.3 | | ns |
| Rise Time | t _r | | | 9.8 | | ns |
| Turn-OFF Delay Time | t _d (off) | | | 40 | | ns |
| Fall Time | tf | | | 24 | | ns |
| Total Gate Charge | Qg | V _{DS} =30V, V _{GS} =10V, I _D =4.5A | | 10 | | nC |
| Gate to Source Charge | Qgs | | | 1.6 | | nC |
| Gate to Drain "Miller" Charge | Qgd | | | 2.1 | | nC |
| Diode Forward Voltage | V _{SD} | I _S =4.5A, V _{GS} =0V | | 0.83 | 1.2 | V |

Switching Time Test Circuit









0

20

60

80

Ambient Temperature, Ta - °C

100

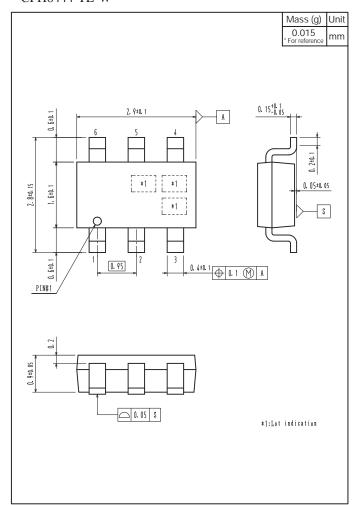
140

160

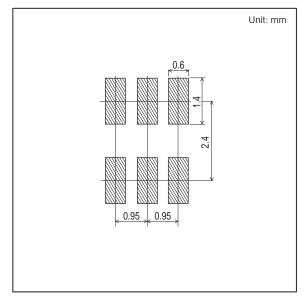
IT13788

Outline Drawing

CPH6444-TL-W



Land Pattern Example



Note on usage: Since the CPH6444 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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